



SOP8 Plastic-Encapsulate MOSFETS

CCM090N04LQA 40V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	7.0mΩ@10V	25A
	9.0mΩ@4.5V	

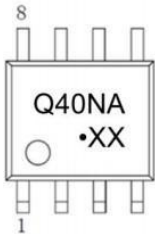
Feature

- High density cell design for ultra low $R_{DS(ON)}$
- Excellent package for good heat dissipation
- AEC Q101 Qualified

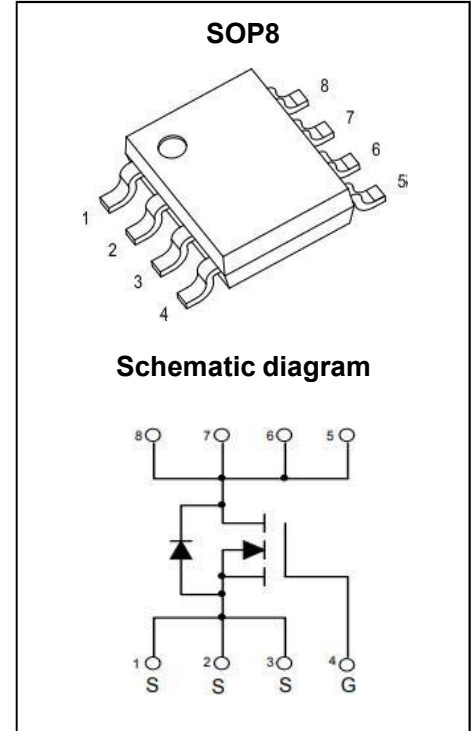
Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

MARKING:



Q40NA = Device Code
XX = Date Code



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DS}	40	V	
Gate-Source Voltage	V_{GS}	±20	V	
Continuous Drain Current	I_D	$T_c = 25^\circ\text{C}$	25	A
		$T_c = 100^\circ\text{C}$	17.5	A
Pulsed Drain Current	I_{DM}	100	A	
Single Pulsed Avalanche Energy	E_{AS}	100	mJ	
Power Dissipation	P_D	3.6	W	
Thermal Resistance from Junction to Ambient ¹	$R_{\theta JA}$	41	$^\circ\text{C/W}$	
Junction Temperature	T_J	175	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55~ +175	$^\circ\text{C}$	

* E_{AS} Test Condition $V_{DD} = 25\text{V}$, $V_{GS} = 10\text{V}$, $L = 0.5\text{mH}$, $I_{AS} = 20\text{A}$ Starting $T_J = 25^\circ\text{C}$.

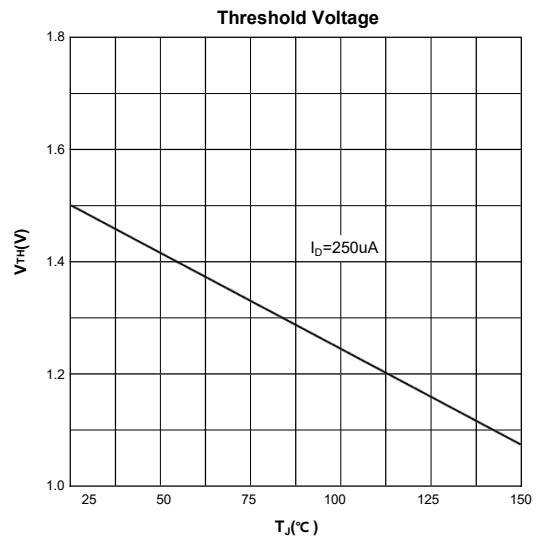
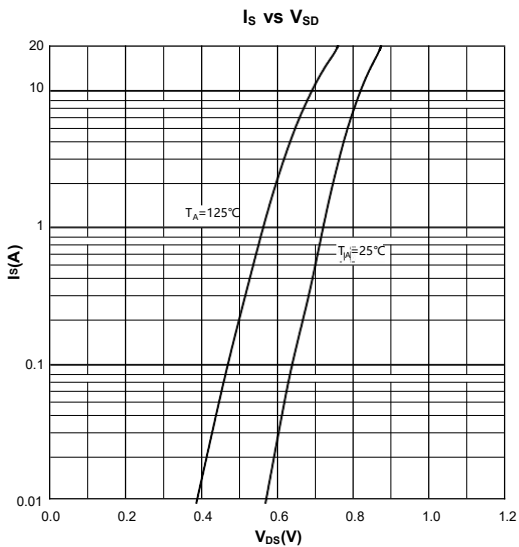
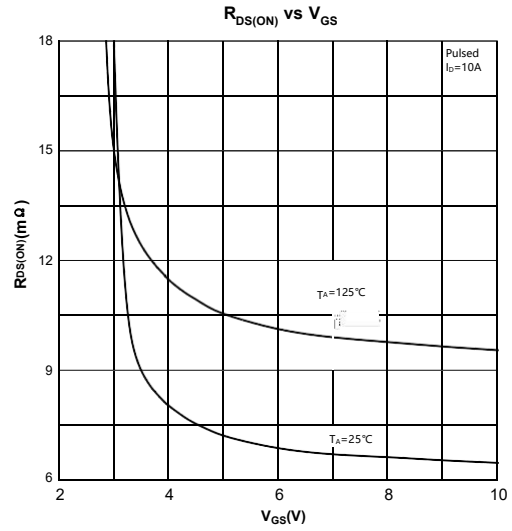
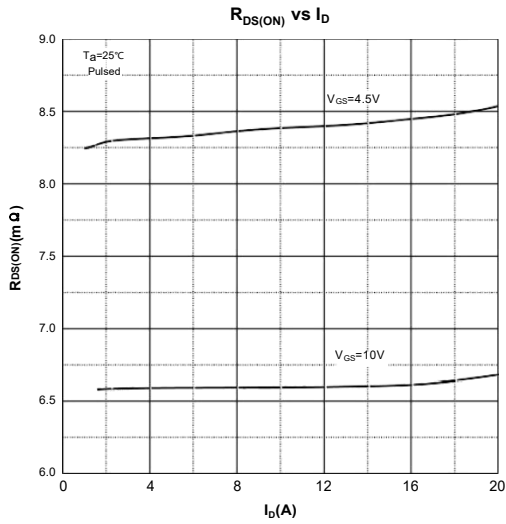
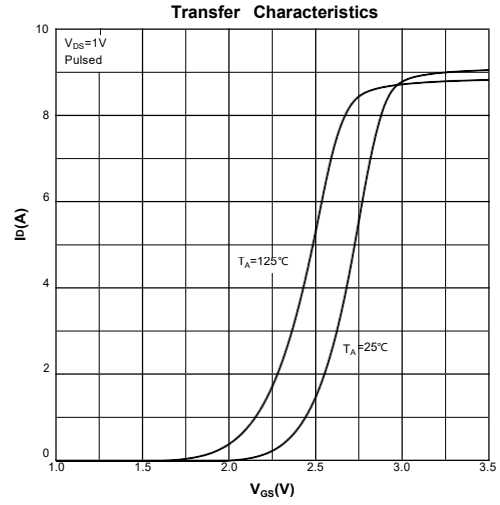
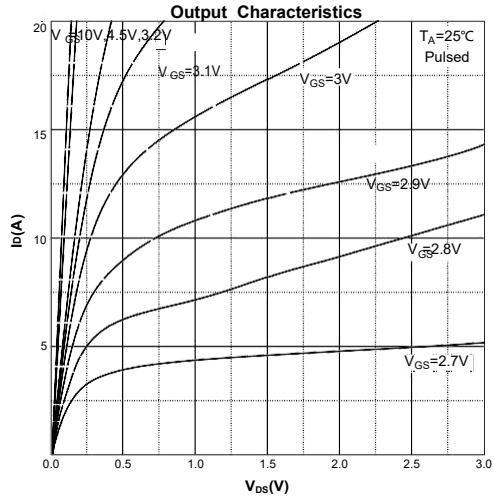
MOSFET ELECTRICAL CHARACTERISTICS(T_A = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	40			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 40V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2.5	V
Drainsource onresistance	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		7	9	mΩ
		V _{GS} = 4.5V, I _D = 10A		9	13.5	
Forward transconductance	g _{FS}	V _{DS} = 10V, I _D = 10A		13		S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz		2775		pF
Output Capacitance	C _{oss}			195		
Reverse Transfer Capacitance	C _{rss}			165		
Gate resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		1.72		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 20V, V _{GS} = 10V, I _D = 10A		20		nC
GateSource Charge	Q _{gs}			3.5		
GateDrain Charge	Q _{gd}			5		
Turnon delay time	t _{d(on)}	V _{DD} = 15V, R _G = 3Ω, V _{GS} = 10V, R _L = 3Ω		12		ns
Turnon rise time	t _r			3		
Turnoff delay time	t _{d(off)}			50		
Turnoff fall time	t _f			5		
Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 10A			1.2	V

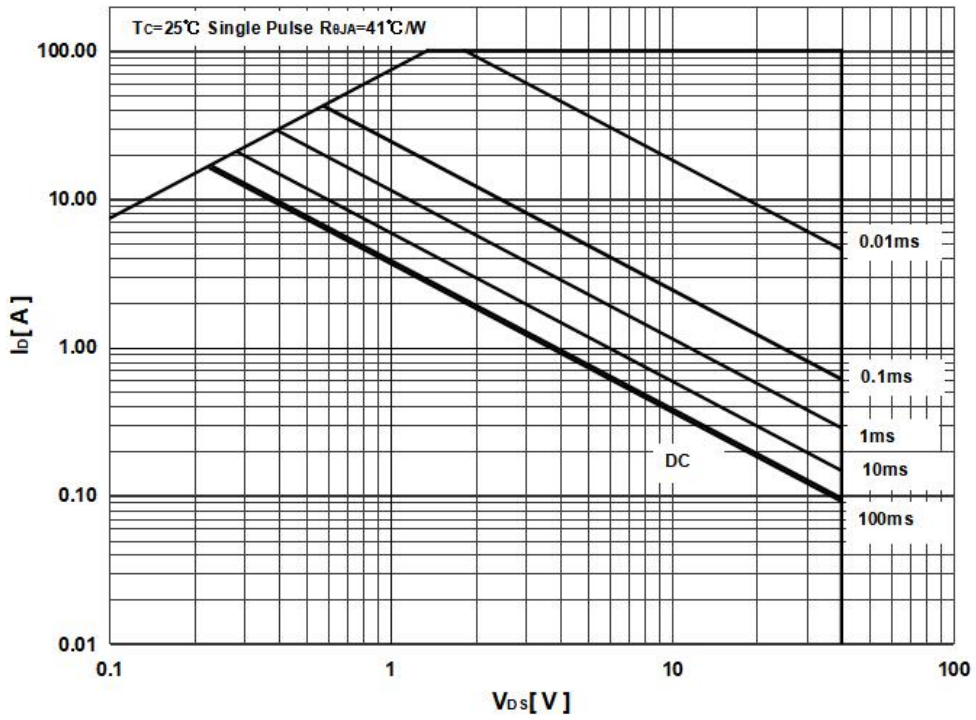
Notes :

1.R_{θJA} is measured with the device mounted on 1 in² FR4 board with 1oz. single side copper, in a still air environment with T_A =25°C.

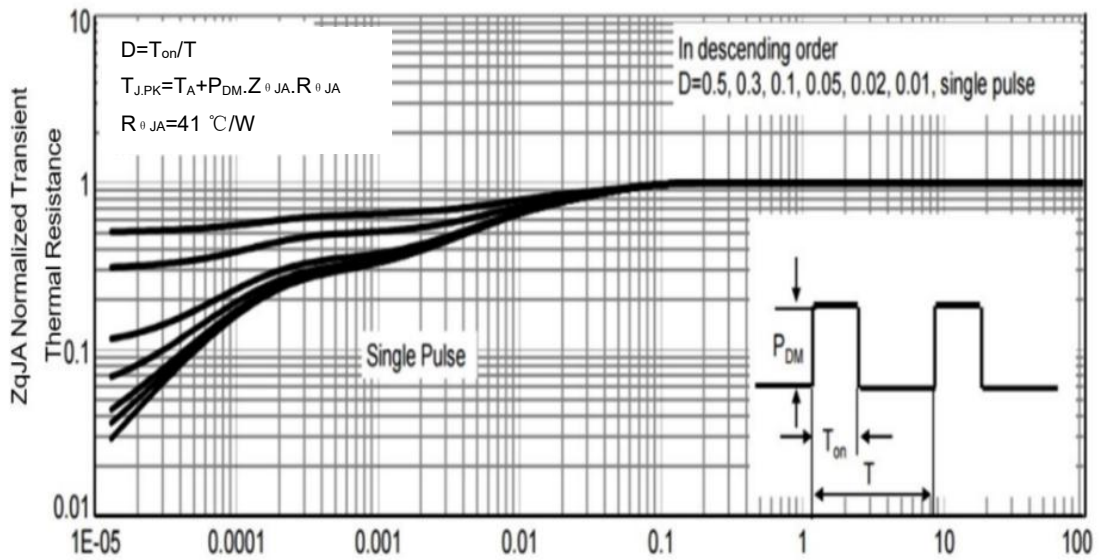
Typical Characteristics



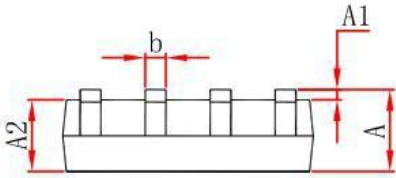
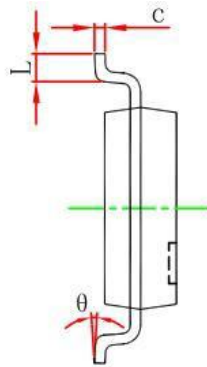
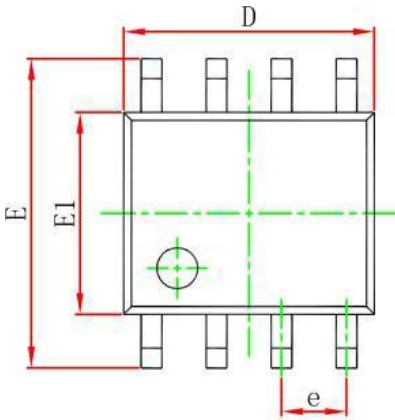
Maximum Forward Biased Safe Operating Area



Normalized Thermal Transient Impedance



SOP8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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Date of change	Rev #	revise content
2023/2/24	A/0	/